ELECTRICAL CHARACTERISTICS (TA = +25°C)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	Ісво	VcB = 5 V, I∈ = 0 mA	-	-	100	nA
Emitter Cut-off Current	Ево	V _{EB} = 1 V, lc = 0 mA	-	-	100	nA
DC Current Gain	hre Note 1	VcE = 2 V, lc = 5 mA	130	190	260	-
RF Characteristics						
Gain Bandw idth Product	f⊤	Vce = 3 V, lc = 20 mA, f = 2 GHz	20	25	_	GHz
Insertion Pow er Gain	S _{21e} 2	Vce = 3 V, lc = 20 mA, f = 2 GHz	16.0	18.0	-	dB
Noise Figure (1)	NF	$\begin{split} &V_{CE}=2~V,~lc=5~mA,~f=2~GHz,\\ &Z_{S}=Z_{Sopt},~Z_{L}=Z_{Lopt} \end{split}$	_	0.8	1.1	dB
Noise Figure (2)	NF	$V_{CE} = 2 \text{ V}, \text{ lc} = 5 \text{ mA}, \text{ f} = 5.2 \text{ GHz},$ $Z_{S} = Z_{Sopt}, Z_{L} = Z_{Lopt}$	-	1.3	_	dB
Associated Gain (1)	Ga	$V_{CE} = 2 \text{ V}, \text{ lc} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz},$ $Z_{S} = Z_{Sopt}, Z_{L} = Z_{Lopt}$	15.0	17.0	_	dB
Associated Gain (2)	Ga	$V_{CE} = 2 \text{ V}, \text{ lc} = 5 \text{ mA}, \text{ f} = 5.2 \text{ GHz},$ $Z_{S} = Z_{Sopt}, Z_{L} = Z_{Lopt}$	-	10.0	_	dB
Reverse Transfer Capacitance	Cre Note 2	Vсв = 2 V, IE = 0 mA, f = 1 MHz	_	0.15	0.25	pF
Maximum Stable Pow er Gain	MSG Note	VcE = 3 V, lc = 20 mA, f = 2 GHz	19.0	21.5	-	dB
Gain 1 dB Compression Output Pow er	Po (1 dB)	$\begin{split} &V_{CE}=3~V,~lc=20~mA,~f=2~GHz,\\ &Z_{S}=Z_{Sopt},~Z_{L}=Z_{Lopt} \end{split}$	-	13	-	dBm
3rd Order Intermodulation Distortion Output Intercept Point	OIP ₃	$\begin{split} &\text{Vce} = 3 \text{ V, lc} = 20 \text{ mA, f} = 2 \text{ GHz,} \\ &\text{Zs} = Z \text{sopt, ZL} = Z \text{Lopt} \end{split}$	_	23	-	dBm

Notes 1. Pulse measurement: PW \leq 350 μ s, Duty Cycle \leq 2%

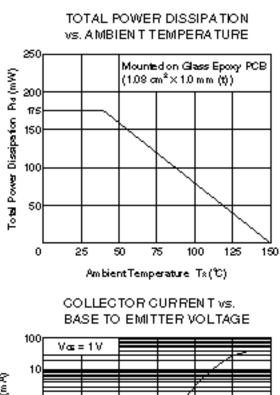
2. Collector to base capacitance when the emitter grounded

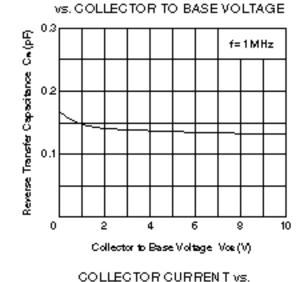
3. MSG =
$$\frac{|S_{21}|}{|S_{12}|}$$

hfe CLASSIFICATION

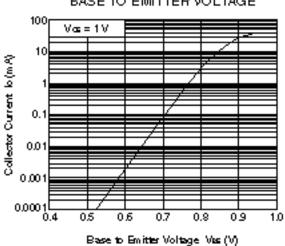
Rank	FB		
Marking	T1H		
hre Value	130 to 260		

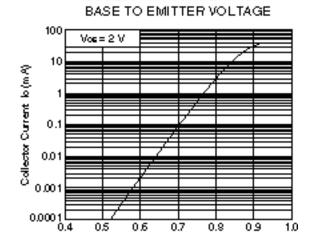
★ TYPICAL CHARACTERISTICS (T_A = +25°C, unless otherwise specified)

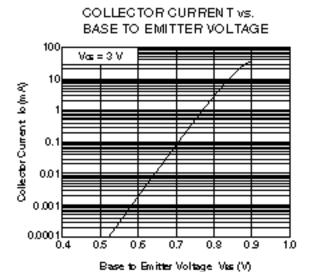


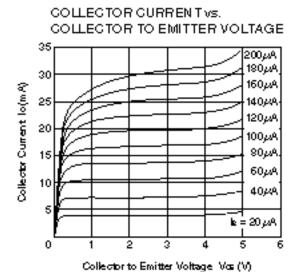


REVERSE TRANSFER CAPACITANCE







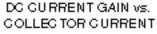


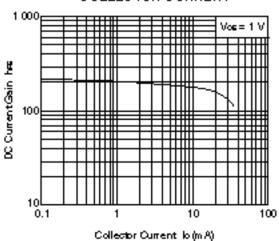
Base to Emitter Voltage Vas (V)

3

Vos= 2 V

100





Sourcest Gain ha

Collector Current to (m.A)

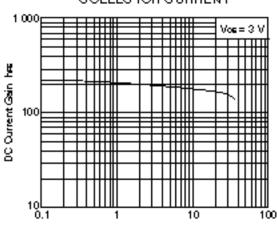
DC GURRENT GAIN vs.

COLLECTOR GURRENT

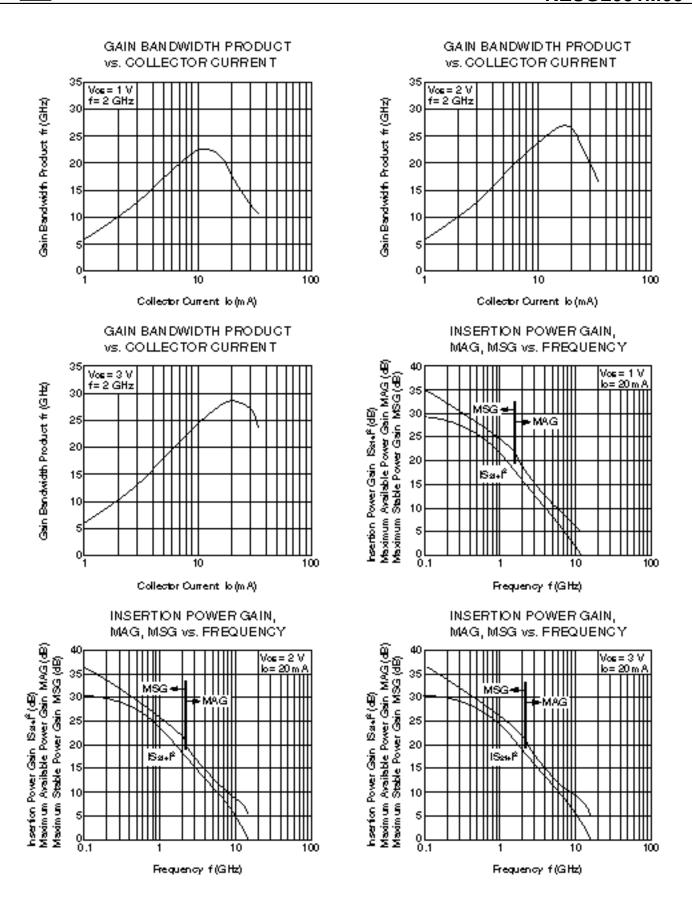
1 0000

10L 0.1

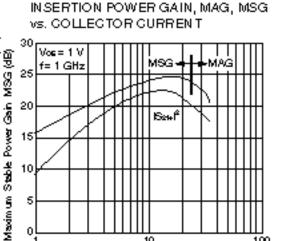
DC GURRENT GAIN vs. GOLLECTOR GURRENT



Collector Current Io (m.A)



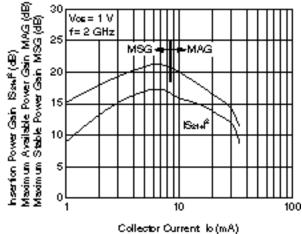
hserian Power Gain ISsuff (dB) Maximum Available Power Gain MAG (dB)



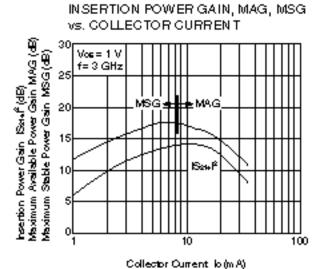
10 Collector Current lo (m.A)

100

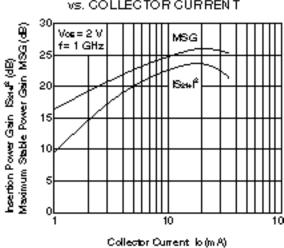
INSERTION POWER GAIN, MAG, MSG vs. GOLLEGTOR GURRENT



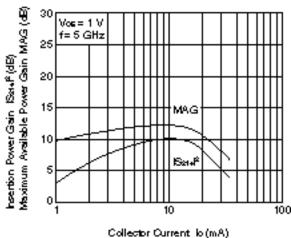
INSERTION POWER GAIN, MAG



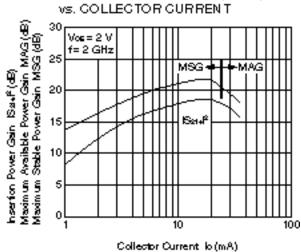
INSERTION POWER GAIN, MSG vs. COLLECTOR CURRENT

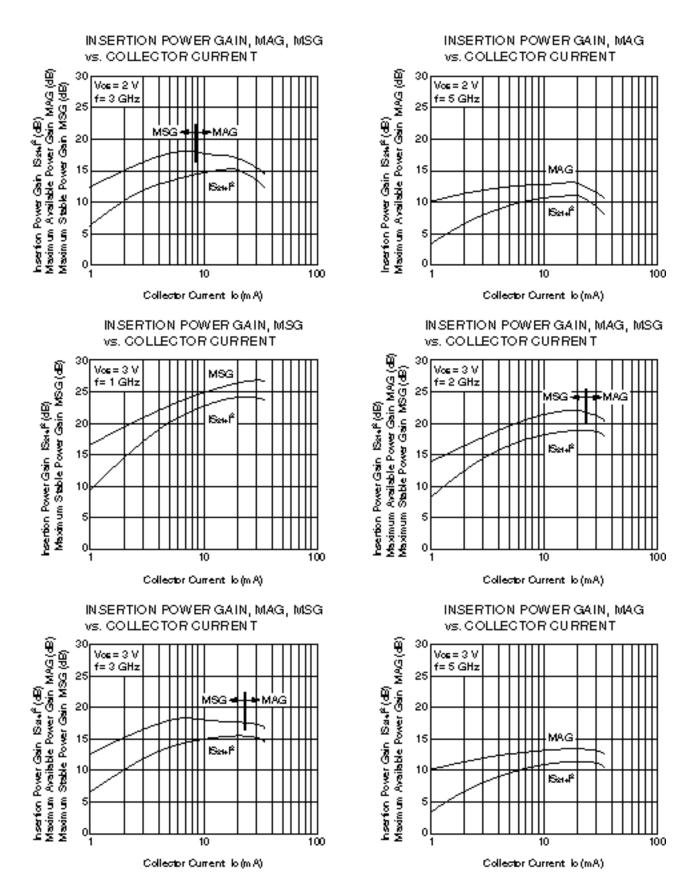


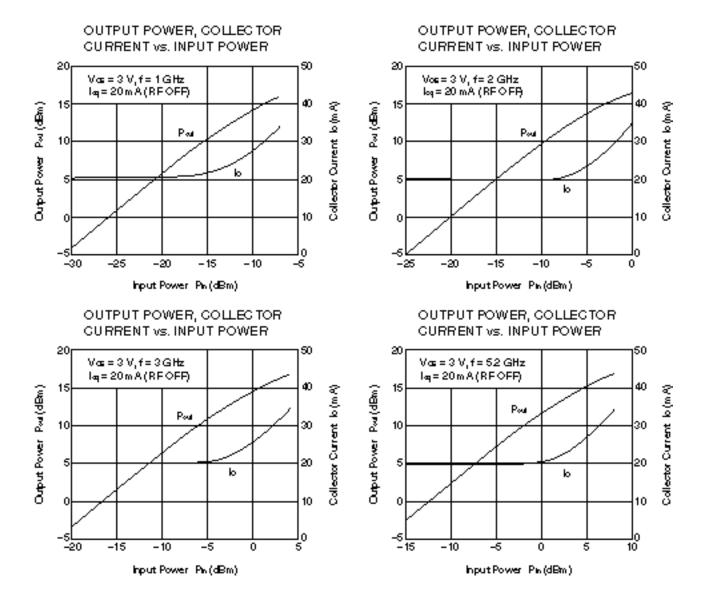
vs. COLLECTOR CURRENT

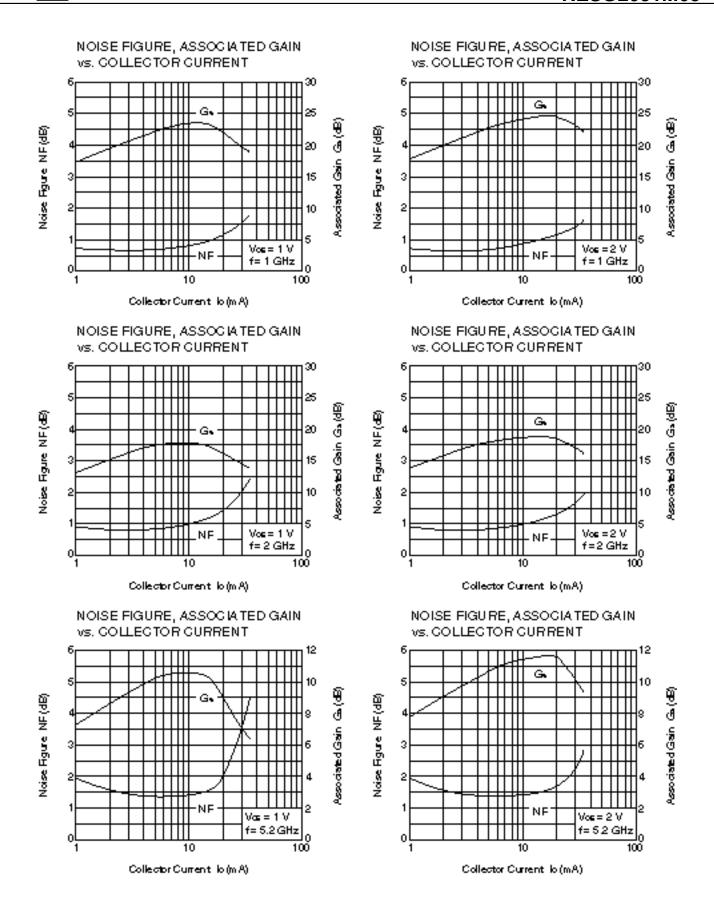


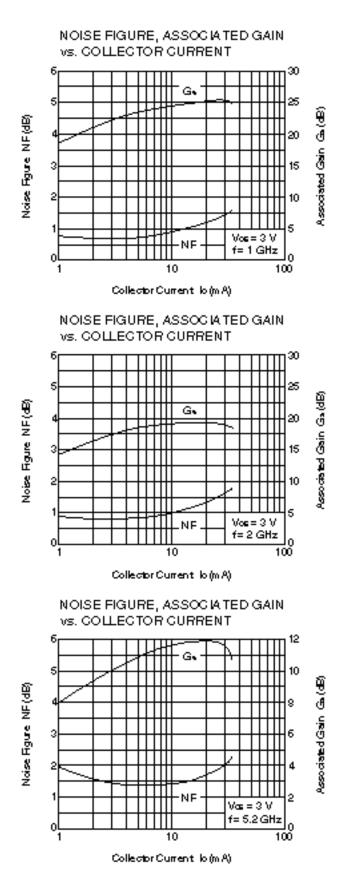
INSERTION POWER GAIN, MAG, MSG











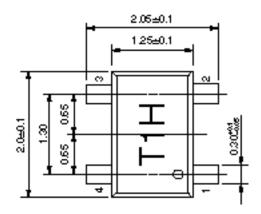
Remark The graphs indicate nominal characteristics.

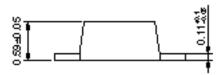
S-PARAMETERS

- S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.
- · Click here to download S-parameters.
- [RF and Microwave] ® [Device Parameters]
- URL http://www.necel.com/microwave/en/

PACKAGE DIMENSIONS

FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M05) (UNIT: mm)





PIN CONNECTIONS

- 1. Base
- 2. Emitter
- 3. Collector
- 4. Emitter